MCMA25P1200TA

=

=

 V_{RRM}

I TAV

VT

= 2x 1200 V

25 A

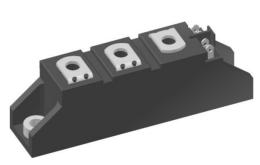
1.2 V

Phase le	эg
----------	----

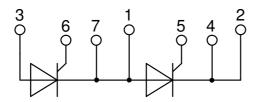
Т

Part number

MCMA25P1200TA



Backside: isolated **E**72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

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Data according to IEC 60747and per semiconductor unless otherwise specified

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MCMA25P1200TA

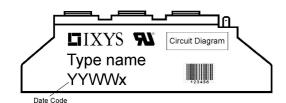
Thyristo				1	Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	0 0	$T_{VJ} = 25^{\circ}C$			1300	\
V _{RRM/DRM}	max. repetitive reverse/forward bl		$T_{VJ} = 25^{\circ}C$			1200	١
R/D	reverse current, drain current	V _{R/D} = 1200 V	$T_{vJ} = 25^{\circ}C$			100	μ/
		V _{R/D} = 1200 V	$T_{VJ} = 140^{\circ}C$			4	m/
V _T	forward voltage drop	$I_{T} = 25 A$	$T_{vJ} = 25^{\circ}C$			1.22	١
		$I_{T} = 50 \text{ A}$				1.47	١
		I _T = 25 A	$T_{vJ} = 125^{\circ}C$			1.20	١
		I _T = 50 A				1.52	١
I _{tav}	average forward current	$T_c = 85^{\circ}C$	T _{vJ} = 140°C			25	ļ
I _{T(RMS)}	RMS forward current	180° sine				40	ļ
V _{T0}	threshold voltage		T _{v.i} = 140°C			0.87	١
r _T	slope resistance } for power lo	oss calculation only	vo			13	m۵
R _{thJC}	thermal resistance junction to cas	6				1.2	-
R _{thCH}	thermal resistance case to heatsir				0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$		0.20	90	W
	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v_i} = 45^{\circ}C$			400	4
TSM	max formate barge barrow	t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			430	,
		t = 0.5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$\frac{V_{R}}{T_{V,I}} = 140^{\circ}C$			340	, ,
101	under for function	t = 8,3 ms; (60 Hz), sine	$\frac{V_{R} = 0 V}{T_{R} + 1500}$			365	4
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			800	A ²
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			770	A ²
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 140 ^{\circ}\text{C}$			580	A ²
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			555	A ²
C	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{vJ} = 25^{\circ}C$		16		pl
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 140^{\circ}C$			10	V
		t _P = 300 μs				5	v
P _{GAV}	average gate power dissipation					0.5	V
(di/dt) _{cr}	critical rate of rise of current	T _{vJ} = 125 °C; f = 50 Hz re	epetitive, $I_{T} = 75 A$			150	A/μ
	$t_{P} = 200 \mu s; di_{G}/dt = 0.45 A/\mu s;$						
		$I_{G} = 0.45 \text{ A}; \text{ V} = \frac{2}{3} \text{ V}_{DRM}$ no	on-repet., $I_{\tau} = 25 \text{ A}$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DBM}$	T _{vJ} = 125°C			1000	V/µ
		$R_{GK} = \infty$; method 1 (linear volta	ge rise)				
V _{gt}	gate trigger voltage	$V_{\rm D} = 6 \text{ V}$	$T_{vJ} = 25^{\circ}C$			1.5	١
- 01			$T_{vJ} = -40^{\circ}C$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			55	m/
GI	gale ligger carent	• _D = 0 •	$T_{vj} = -40^{\circ}C$			80	m/
V _{gd}	gate non-trigger voltage	$V_{D} = \frac{2}{3} V_{DBM}$	$T_{VJ} = -40^{\circ}C$ $T_{VJ} = 140^{\circ}C$			0.2	۱
	gate non-trigger current	$\mathbf{v}_{\mathrm{D}} = 73 \mathbf{v}_{\mathrm{DRM}}$	1 _{VJ} = 140 O			5	i .
		10	T 0500				m/
I.	latching current	$t_p = 10 \ \mu s$	$T_{vJ} = 25^{\circ}C$			150	m/
_		$I_{\rm G} = 0.45 \text{A}; di_{\rm G}/dt = 0.45 \text{A}/\mu\text{s}$					
I _H	holding current	$V_{D} = 6 V R_{GK} = \infty$	$T_{VJ} = 25 \degree C$			100	m/
t _{gd}	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{vJ} = 25 ^{\circ}C$			2	μ
		$I_{G} = 0.45 \text{ A}; \ di_{G}/dt = 0.45 \text{ A}/\mu s$, , , ,
t _q	turn-off time	$V_{R} = 100 \text{ V}; I_{T} = 25 \text{ A}; \text{ V} = 27$	⅓ V _{DRM} T _{VJ} =125 °C		150		μ
		$di/dt = 10 \text{ A}/\mu \text{s} dv/dt = 20 \text{ V}/\mu$	/us_t_ = 200 us				1

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MCMA25P1200TA

Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					60	Α
T _{vj}	virtual junction temperature	9			-40		140	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	araanaa diatanaa an aurf	ace striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on suna	ace striking distance through an	terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			4800			V
	t = 1 minute		50/60 Hz, RMS; liso∟ ≤ 1 mA		4000			V



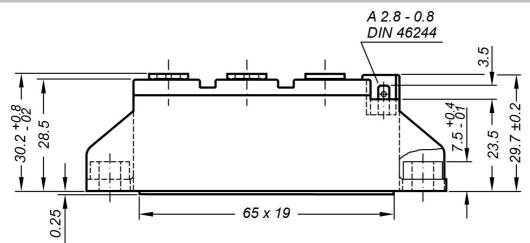
Part description

M = Module C = Thyristor (SCR) M = Thyristor A = (up to 1800V) 25 = Current Rating [A] P = Phase leg 1200 = Reverse Voltage [V] TA = TO-240AA-1B

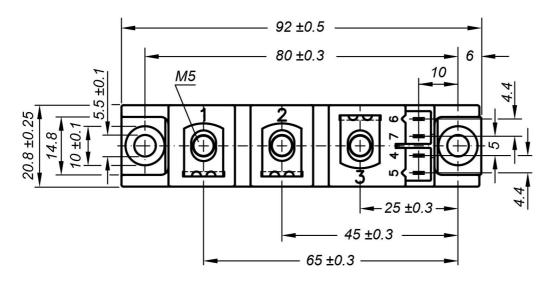
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA25P1200TA	MCMA25P1200TA	Box	36	514481

Equiv	alent Circuits for	Simulation	* on die level	T _{vj} = 140 °C
)- <u>R</u>	Thyristor		
$V_{0 max}$	threshold voltage	0.87		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	11.8		mΩ

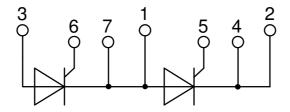
Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"

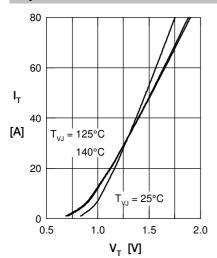


Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)



MCMA25P1200TA

Thyristor



400

300

200

100

100.0

10.0

1.0

0.1

0.01

0.10

t_{gd}

[µs]

 $T_{VJ} = 140^{\circ}C$

0.1

t [s]

 \mathbf{I}_{TSM} : crest value, t: duration

T_{VJ} = 25°C

1.00

I_G [A]

Fig. 5 Gate controlled delay time t_{ad}

lim

10.00

Fig. 2 Surge overload current

0.01

ITSM

[A]

50 Hz, 80% V

Fig. 1 Forward characteristics

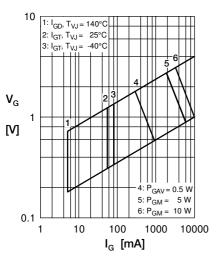


Fig. 4 Gate voltage & gate current

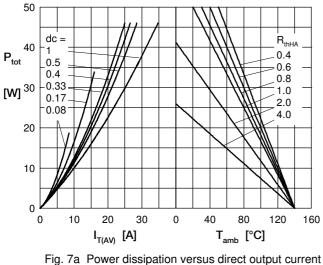


Fig. 7b and ambient temperature

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